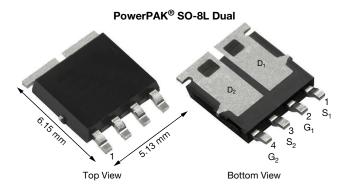
SQJ912DEP

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Vishay Siliconix

Automotive Dual N-Channel 40 V (D-S) 175 °C MOSFET

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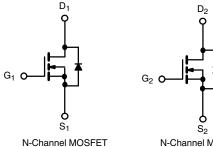


- TrenchFET[®] power MOSFET
- AEC-Q101 qualified
- 100 % R_q and UIS tested
- Material categorization: for definitions of compliance please see www.vishay.com/doc?99912



RoHS COMPLIANT HALOGEN FREE

PRODUCT SUMMARY	1
V _{DS} (V)	40
$R_{DS(on)}\left(\Omega\right)$ at V_{GS} = 10 V	0.0073
$R_{DS(on)}\left(\Omega\right)$ at V_{GS} = 4.5 V	0.0102
I _D (A) per leg	30
Configuration	Dual
Package	PowerPAK SO-8L



N-Channel MOSFET

ABSOLUTE MAXIMUM RATING	S (T _C = 25 °C, unless	s otherwise noted)	
PARAMETER		SYMBOL	LIMIT	UNIT
Drain-source voltage		V _{DS}	40	V
Gate-source voltage		V _{GS}	± 20	v
Continuous drain current	T _C = 25 °C ^a	Ŀ	30	
	T _C = 125 °C	Ι _D	26	
Continuous source current (diode conduction	ו) ^a	I _S	25	А
Pulsed drain current ^b		I _{DM}	120	
Single pulse avalanche current	L = 0.1 mH	I _{AS}	19	
Single pulse avalanche energy		E _{AS}	18	mJ
Martin and a state to the b	T _C = 25 °C	D	27	W
Maximum power dissipation ^b	T _C = 125 °C	PD	9	
Operating junction and storage temperature range		T _J , T _{stg}	-55 to +175	°C
Soldering recommendations (peak temperatu		260	0	

THERMAL RESISTANCE RATINGS				
PARAMETER		SYMBOL	LIMIT	UNIT
Junction-to-ambient	PCB mount ^c	R _{thJA}	85	°C/W
Junction-to-case (drain)		R _{thJC}	5.5	0/W

Notes

- a. Package limited
- b. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %
- c. When mounted on 1" square PCB (FR4 material)
- d. See solder profile (www.vishav.com/doc?73257). The PowerPAK SO-8L is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection
- e. Rework conditions: manual soldering with a soldering iron is not recommended for leadless components

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SPECIFICATIONS (T _C = 25 °C, u	nless otherv	vise noted)						
PARAMETER	SYMBOL	TES	MIN.	TYP.	MAX.	UNIT		
Static								
Drain-source breakdown voltage	V _{DS}	V_{GS} = 0 V, I _D = 250 µA		40	-	-	V	
Gate-source threshold voltage	V _{GS(th)}	V _{DS} =	- V _{GS} , I _D = 250 μA	1.5	2.0	2.5	v	
Gate-source leakage	I _{GSS}	V _{DS} =	0 V, V_{GS} = ± 20 V	-	-	± 100	nA	
	I _{DSS}	$V_{GS} = 0 V$	V _{DS} = 40 V	-	-	1		
Zero gate voltage drain current		$V_{GS} = 0 V$	$V_{DS} = 40 \text{ V}, \text{ T}_{J} = 125 ^{\circ}\text{C}$	-	-	50	μA	
		$V_{GS} = 0 V$	$V_{DS} = 40 \text{ V}, \text{ T}_{J} = 175 ^{\circ}\text{C}$	-	-	150		
On-state drain current ^a	I _{D(on)}	$V_{GS} = 10 V$	$V_{DS} \ge 5 V$	15	-	-	А	
		$V_{GS} = 10 \text{ V}$	I _D = 7 A	-	0.0059	0.0073		
Ducin courses on state registernes 3	Б	$V_{GS} = 4.5 V$	I _D = 5 A	-	0.0082	0.0102		
Drain-source on-state resistance ^a	R _{DS(on)}	V _{GS} = 10 V	I _D = 7 A, T _J = 125 °C	-	-	0.0106	12	
		$V_{GS} = 10 \text{ V}$	I _D = 7 A, T _J = 175 °C	-	-	0.0125	μΑ Α 3 2 6 5 5 8	
Forward transconductance ^b	9 _{fs}	V _{DS} = 15 V, I _D = 7 A		-	47	-	S	
Dynamic ^b								
Input capacitance	C _{iss}		V _{DS} = 25 V, f = 1 MHz	-	1246	1745	pF	
Output capacitance	C _{oss}	$V_{GS} = 0 V$		-	345	483		
Reverse transfer capacitance	C _{rss}			-	31	44		
Total gate charge ^c	Qg			-	24	36	nC	
Gate-source charge ^c	Q _{gs}	$V_{GS} = 10 V$	$V_{DS} = 20 \text{ V}, I_D = 11.3 \text{ A}$	-	5	-		
Gate-drain charge ^c	Q _{gd}			-	5	-		
Gate resistance	Rg	f = 1 MHz		1.4	2.8	4.2	Ω	
Turn-on delay time ^c	t _{d(on)}			-	10	20		
Rise time ^c	t _r	$V_{DD} = 20 \text{ V}, \text{ R}_{L} = 20 \Omega$		-	4	10	ns	
Turn-off delay time ^c	t _{d(off)}	I _D ≅ 1 A, \	$I_D \cong 1 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$		25	50		
Fall time ^c	t _f			-	21	35		
Source-Drain Diode Ratings and Charac	teristics ^b							
Pulsed current ^a	I _{SM}			-	-	120	А	
Forward voltage	V _{SD}	$I_F = 7 \text{ A}, \text{ V}_{GS} = 0 \text{ V}$		-	0.79	1.2	V	
Body diode reverse recovery time	t _{rr}			-	25	50	ns	
Body diode reverse recovery charge	Qrr		$\Lambda di/dt = 100 \Lambda/ma$	-	16	32	nC	
Reverse recovery fall time	t _a	I _F = 4 A, di/dt = 100 A/μs		-	11	-	ns	
Reverse recovery rise time	t _b			-	14	-	ns	

Notes

a. Pulse test; pulse width \leq 300 µs, duty cycle \leq 2 %

b. Guaranteed by design, not subject to production testing

c. Independent of operating temperature

Body diode peak reverse recovery current

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

I_{RM(REC)}

2 For technical questions, contact: automostechsupport@vishay.com А

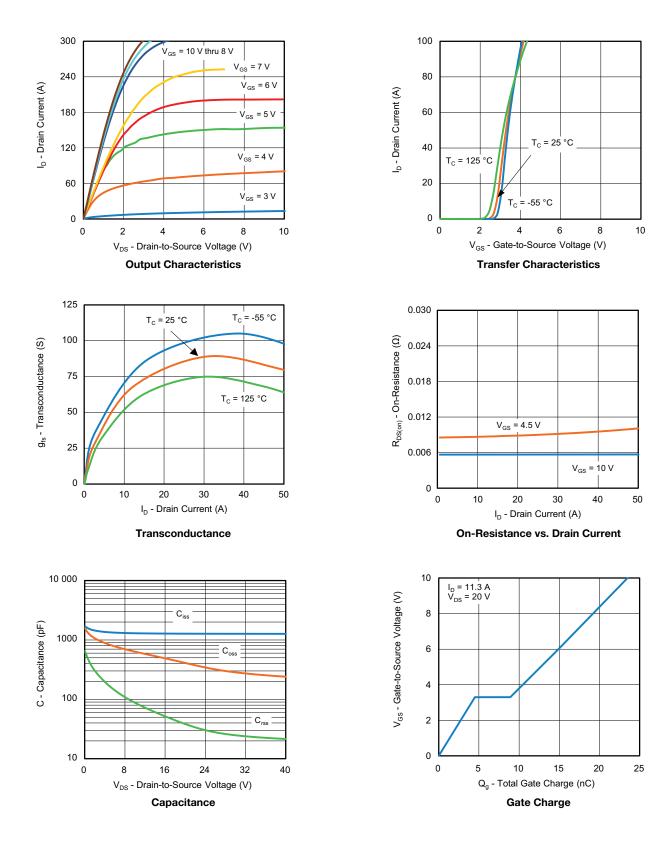
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TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)



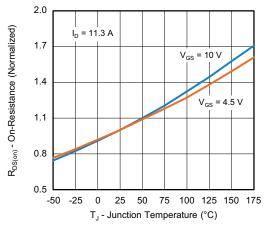
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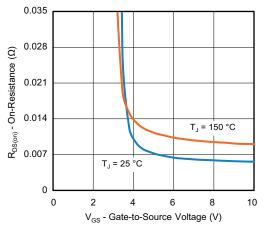
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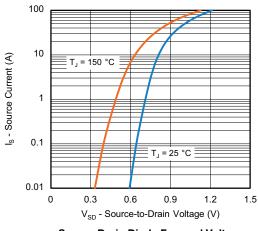
TYPICAL CHARACTERISTICS ($T_A = 25 \text{ °C}$, unless otherwise noted)



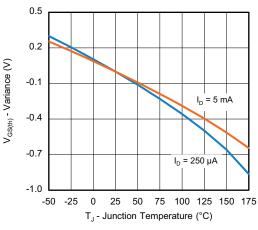
On-Resistance vs. Junction Temperature



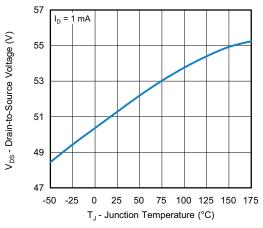
On-Resistance vs. Gate-to-Source Voltage



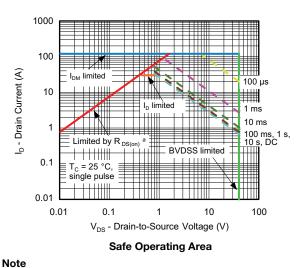
Source Drain Diode Forward Voltage



Threshold Voltage



Drain Source Breakdown vs. Junction Temperature



a. V_{GS} > minimum V_{GS} at which $R_{DS(on)}$ is specified

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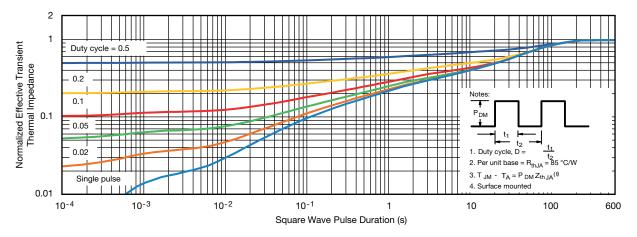
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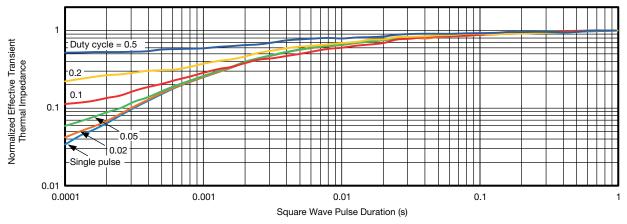
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THERMAL RATINGS (T_A = 25 °C, unless otherwise noted)



Normalized Thermal Transient Impedance, Junction-to-Ambient



Normalized Thermal Transient Impedance, Junction-to-Case

Note

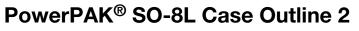
- The characteristics shown in the two graphs
- Normalized Transient Thermal Impedance Junction-to-Ambient (25 °C)
- Normalized Transient Thermal Impedance Junction-to-Case (25 °C)

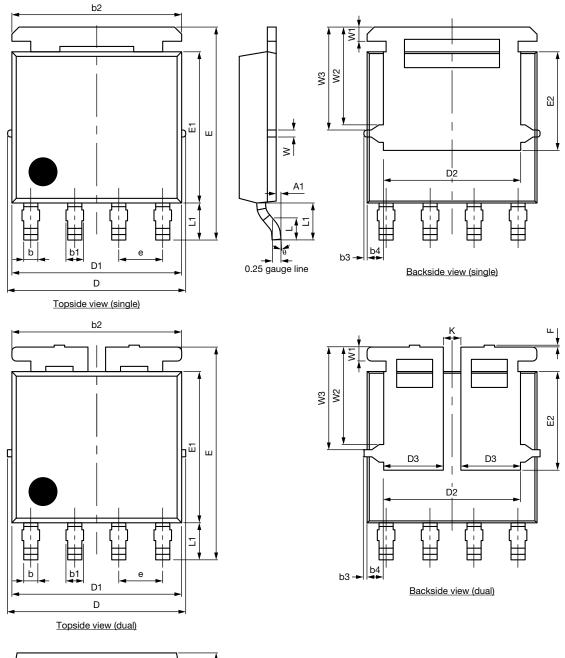
are given for general guidelines only to enable the user to get a "ball park" indication of part capabilities. The data are extracted from single pulse transient thermal impedance characteristics which are developed from empirical measurements. The latter is valid for the part mounted on printed circuit board - FR4, size 1" x 1" x 0.062", double sided with 2 oz. copper, 100 % on both sides. The part capabilities can widely vary depending on actual application parameters and operating conditions

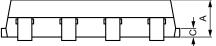
Vishay Siliconix maintains worldwide manufacturing capability. Products may be manufactured at one of several qualified locations. Reliability data for Silicon Technology and Package Reliability represent a composite of all qualified locations. For related documents such as package / tape drawings, part marking, and reliability data, see www.vishay.com/ppg?77568.

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1 For technical questions, contact: pmostechsupport@vishay.com

Package Information



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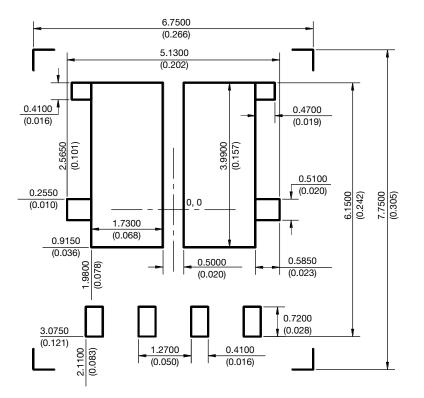
DIM.		MILLIMETERS			INCHES			
	MIN.	MIN. NOM. MAX			MIN. NOM.			
А	1.00	1.07	1.14	0.039	0.042	0.045		
A1	0.00	-	0.127	0.00	-	0.005		
b	0.33	0.41	0.48	0.013	0.016	0.019		
b1	0.44	0.51	0.58	0.017	0.020	0.023		
b2	4.80	4.90	5.00	0.189	0.193	0.197		
b3		0.094	•		0.004			
b4		0.47			0.019			
С	0.20	0.25	0.30	0.008	0.010	0.012		
D	5.00	5.13	5.25	0.197	0.202	0.207		
D1	4.80	4.90	5.00	0.189	0.193	0.197		
D2	3.86	3.96	4.06	0.152	0.156	0.160		
D3	1.63	1.73	1.83	0.064	0.068	0.072		
е		1.27 BSC	•	0.050 BSC				
E	6.05	6.15	6.25	0.238	0.242	0.246		
E1	4.27	4.37	4.47	0.168	0.172	0.176		
E2	2.75	2.85	2.95	0.108	0.112	0.116		
F	-	-	0.15	-	-	0.006		
L	0.62	0.72	0.82	0.024	0.028	0.032		
L1	0.92	1.07	1.22	0.036	0.042	0.048		
К		0.51			0.020			
W		0.23			0.009			
W1		0.41			0.016			
W2		2.82			0.111			
W3		2.96			0.117			
θ	0°	-	10°	0°	-	10°		

Note

• Millimeters will govern



RECOMMENDED MINIMUM PAD FOR PowerPAK® SO-8L DUAL



Recommended Minimum Pads Dimensions in mm (inches) Keep-out 6.75 (0.266) x 7.75 (0.305)

Revision: 07-Feb-12



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